

**1. Scope :**

This specification applies to silicon zerocrossing phototriac chips,  
Device No. ST-0181

**2. Structure :**

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

**3. Size :**

- 3-1. Chip size : 47.2 mils × 47.2 mils (1.200 mm ×1.200mm ).
- 3-2. Chip thickness : 12±1.0 mil (0.305± 0.025 mm ).
- 3-3. Pad area : 5.9 mil × 5.5 mil (0.150 mm ×0.140 mm ).
- 3-4. Pattern drawing : refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak blocking Current	$I_{DRM}$	$V_{DRM}=800V$			100	nA
Peak on-state voltage	$V_{TM}$	$I_{TM}=100mA$		1.6	3	V
Critical rate of Rise voltage	dv/dt		1000			V/μS
Holding current	$I_H$			250		μA
Inhibit Voltage	$V_{INH}$	$I_{DS}=10\mu A$		7	20	V

